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SIDDHARTH INSTITUTE OF ENGINEERING & TECHNOLOGY:: PUTTUR
(AUTONOMOUS)**B.Tech I Year II Semester Regular Examinations May 2019****SEMICONDUCTOR PHYSICS**

(Common to ECE, CSE, CSIT)

Time: 3 hours

Max. Marks: 60

PART-A

(Answer all the Questions 5 x 2 = 10 Marks)

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|----------|----------|---|----|
| 1 | a | What are the merits of quantum free electron theory? | 2M |
| | b | Define the word depletion layer. | 2M |
| | c | What is meant by luminescence of optical materials? | 2M |
| | d | Mention the basic principle in the propagation of light signal through the optical fibre. | 2M |
| | e | Define top down and bottom up process. | 2M |

PART-B

(Answer all Five Units 5 x 10 = 50 Marks)

UNIT-I

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| 2 | a | What are the salient features of classical free electron theory? Derive an expression for electrical conductivity in a metal. | 7M |
| | b | Mention its drawbacks. | 3M |

OR

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|----------|----------|--|----|
| 3 | a | Define the terms i) Mean free path ii) Relaxation time iii) Mobility. | 6M |
| | b | Find the mobility of electrons in copper if there are 9×10^{28} valence electrons/m ³ and the conductivity of copper is 6×10^7 mho/m? | 4M |

UNIT-II

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|----------|----------|---|----|
| 4 | a | Obtain the conductivity of intrinsic semiconductor with relevant expressions? | 5M |
| | b | The following data are given for an intrinsic Ge at 300K. Calculate the conductivity and resistivity of the sample. ($n_i = 2.4 \times 10^{19} \text{m}^{-3}$, $\mu_e = 0.39 \text{m}^2\text{-V}^{-1}\text{S}^{-1}$, $\mu_p = 0.19 \text{m}^2\text{-V}^{-1}\text{S}^{-1}$). | 5M |

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| 5 | a | Describe the Hall Effect in a semiconductors. | 7M |
| | b | Write the applications of Hall Effect. | 3M |

UNIT-III

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| 6 | a | Elucidate broadly radiative and non-radiative mechanisms in semiconductors. | 5M |
| | b | Explain the construction and working mechanism of solar cells with suitable diagrams. | 5M |

OR

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| 7 | a | Describe the construction and working mechanism of solar cells. | 6M |
| | b | Broadly explain the differences between light emitting diodes and photo detectors. | 4M |

UNIT-IV

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| 8 | a | Derive the relation between the various Einstein's coefficients of absorption and emission of Radiation. | 6M |
| | b | Explain population inversion. | 4M |

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| 9 | a | Describe optical fibre communication system. | 6M |
| | b | Mention the application of optical fibre in sensors. | 4M |

UNIT-V

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| 10 | a | Explain why surface area to volume ratio very large for nano materials. | 5M |
| | b | Find the surface area to volume ratio of Sphere using surface area and volume calculation for the given radius is 5 meter. | 5M |

OR

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|-----------|----------|---|----|
| 11 | a | Write the physical properties of carbon nanotubes. | 5M |
| | b | Write the applications of nanomaterial in various fields. | 5M |

END